

MOSFETs Silicon N-Channel MOS (DTMOS II)

TK20E60U

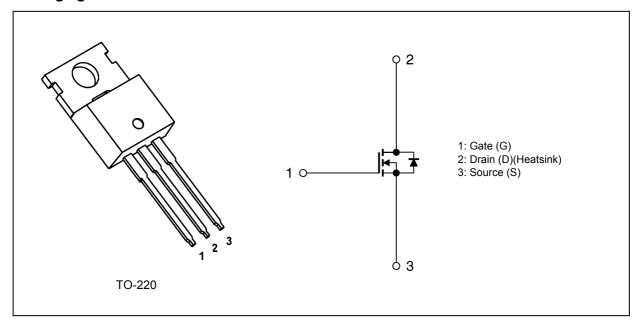
1. Applications

· Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.165 \Omega$ (typ.)
- (2) High forward transfer admittance: $|Y_{fs}| = 12 \text{ S (typ.)}$
- (3) Low leakage current: $I_{\rm DSS}$ = 100 μA (max) (V_{\rm DS} = 600 V)
- (4) Enhancement mode: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_{D} = 1 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics | | | Rating | Unit |
|--------------------------------|-------------------------|------------------|------------|------|
| Drain-source voltage | | V _{DSS} | 600 | V |
| Gate-source voltage | | V _{GSS} | ±30 | |
| Drain current (DC) | (Note 1) | I _D | 20 | Α |
| Drain current (pulsed) | (Note 1) | I _{DP} | 40 | |
| Power dissipation | (T _c = 25°C) | P _D | 190 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 144 | mJ |
| Avalanche current | (Note 3) | I _{AR} | 10 | Α |
| Repetitive avalanche energy | (Note 3) | E _{AR} | 19 | mJ |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 20 | Α |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 40 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | | Max | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 0.658 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 83.3 | |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 2.52 mH, R_G = 25 Ω , I_{AR} = 10 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



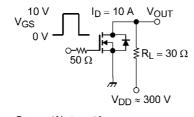
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|------------------------------------------------|-----|-------|------|------|
| Gate leakage current | I _{GSS} | V_{GS} = ±30 V, V_{DS} = 0 V | _ | _ | ±1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 100 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | | V |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 1 mA | 3.0 | _ | 5.0 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 10 A | _ | 0.165 | 0.19 | Ω |
| Forward transfer admittance | Y _{fs} | V _{DS} = 10 V, I _D = 10 A | 3 | 12 | | S |

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|----------------------------------------------------------|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | _ | 1470 | | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 150 | | |
| Output capacitance | C _{oss} | | _ | 3500 | _ | |
| Switching time (rise time) | t _r | See Figure 6.2.1 | _ | 40 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 80 | _ | |
| Switching time (fall time) | t _f | | _ | 12 | _ | |
| Switching time (turn-off time) | t _{off} | | - | 100 | | |



Duty \leq 1%, $t_W = 10 \ \mu s$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------------------|----------|---------------------------------------------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_g | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ | | 27 | 1 | nC |
| Gate-source charge | Q_{gs} | | _ | 16 | _ | |
| Gate-drain charge | Q_{gd} | | _ | 11 | | |

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------|-----------------|-----------------------------------------------|-----|------|------|------|
| Diode forward voltage | V_{DSF} | I _{DR} = 20 A, V _{GS} = 0 V | 1 | | -1.7 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 20 A, V _{GS} = 0 V | _ | 450 | | ns |
| Reverse recovery charge | Q _{rr} | -dl _{DR} /dt = 100 A/μs | _ | 8.1 | _ | μС |



7. Marking

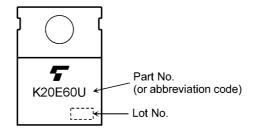


Fig. 7.1 Marking

8. Characteristics Curves (Note)

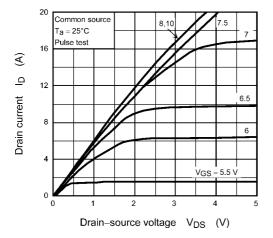


Fig. 8.1 I_D - V_{DS}

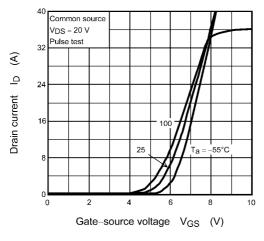


Fig. 8.3 ID - VGS

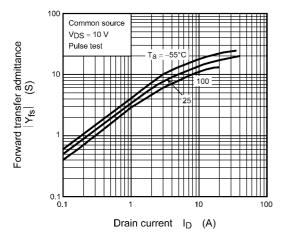


Fig. 8.5 |Yfs| - ID

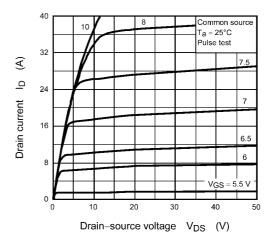


Fig. 8.2 I_D - V_{DS}

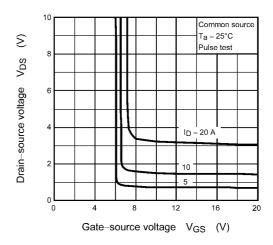


Fig. 8.4 V_{DS} - V_{GS}

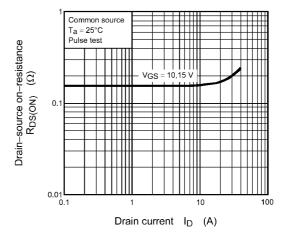


Fig. 8.6 R_{DS(ON)} - I_D

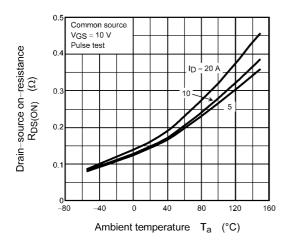


Fig. 8.7 R_{DS(ON)} - T_a

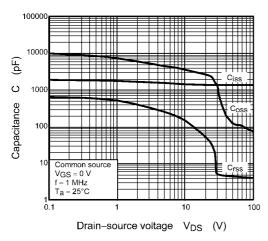


Fig. 8.9 C - V_{DS}

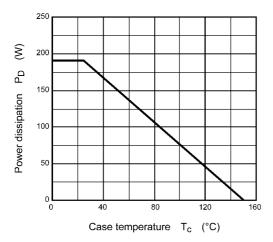


Fig. 8.11 P_D - T_c (Guaranteed Maximum)

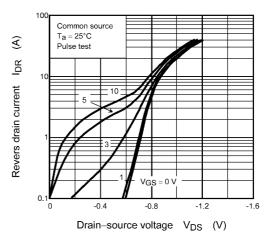


Fig. 8.8 IDR - VDS

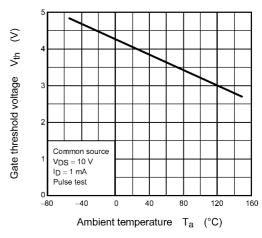


Fig. 8.10 V_{th} - T_a

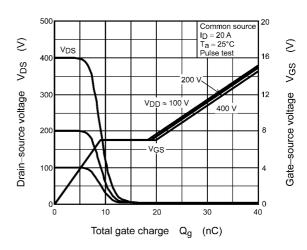


Fig. 8.12 Dynamic Input/Output Characteristics

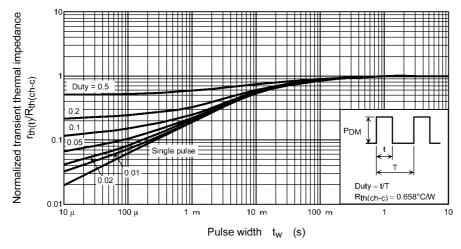


Fig. 8.13 $r_{th}/R_{th(ch-c)} - t_w$ (Guaranteed Maximum)

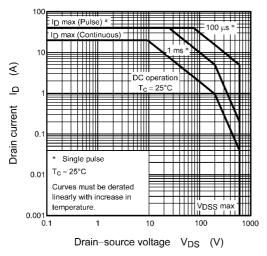


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

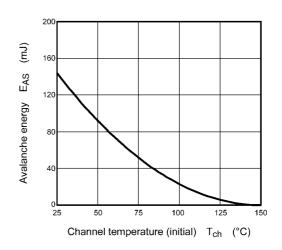


Fig. 8.15 E_{AS} - T_{ch} (Guaranteed Maximum)

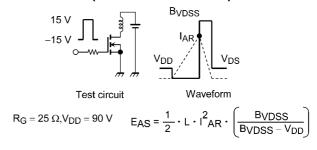
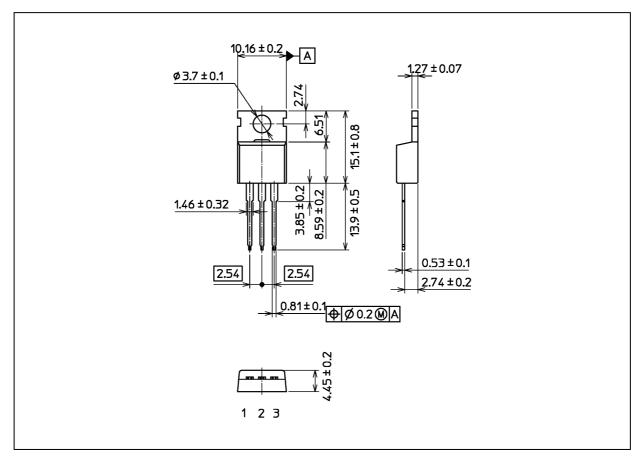


Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 1.93 g (typ.)

| | Package Name(s) |
|------------------|-----------------|
| TOSHIBA: 2-10X1A | |
| Nickname: TO-220 | |



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